

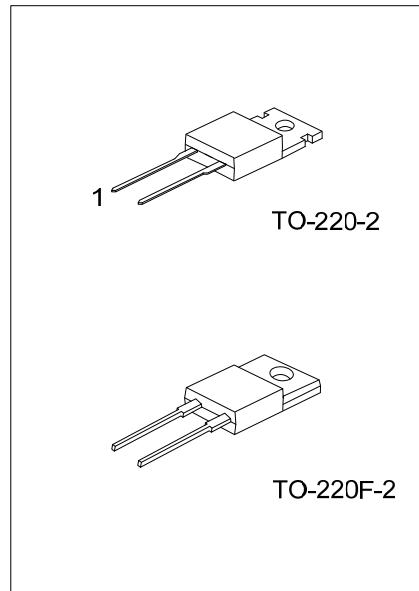
UCBD0665

SiC-SBD DIODE

SILICON CARBIDE SCHOTTKY BARRIER DIODES

■ DESCRIPTION

The **UCBD0665** is an SiC Schottky barrier diodes (SBDs) feature high reverse voltage ratings. In addition to SBDs with short reverse recovery time (trr), provides 650V SBDs with a junction barrier Schottky (JBS) structure that provide low leakage current (Ir) and high surge current capability required for switched-mode power supplies. These devices help improve the efficiency of switched-mode power supplies.



■ FEATURES

- * Negligible reverse recovery
- * High-Frequency Operation
- * Positive Temperature Coefficient
- * Temperature-Independent Switching

■ SYMBOL



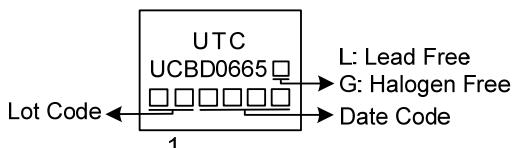
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment		Packing
Lead Free	Halogen Free		1	2	
UCBD0665L-TA2-T	UCBD0665G-TA2-T	TO-220-2	K	A	Tube
UCBD0665L-TF32-R	UCBD0665G-TF32-R	TO-220F-2	K	A	Tube

Note: Pin Assignment: K: Cathode A: Anode

UCBD0665G-TA2-T 	(1)T: Tube (2) TA2: TO-220-2, TF32: TO-220F-2 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz.

PARAMETER	SYMBOL	RATINGS		UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	650		V
Surge Peak Reverse Voltage	V_{RSM}	650		V
Continuous Forward Current	$T_c=25^\circ\text{C}$	I_F	20	A
	$T_c=135^\circ\text{C}$		9	A
	$T_c=153^\circ\text{C}$		6	A
Repetitive Peak Forward Surge Current	$t_p=10\text{ms}$, Half Sine Wave	I_{FRM}	60	A
Non-Repetitive Peak Forward Surge Current		I_{FSM}	66	A
Power Dissipation	TO-220-2	P_D	87	W
	TO-220F-2		40	W
Operating Junction Temperature	T_J		+150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}		-65 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

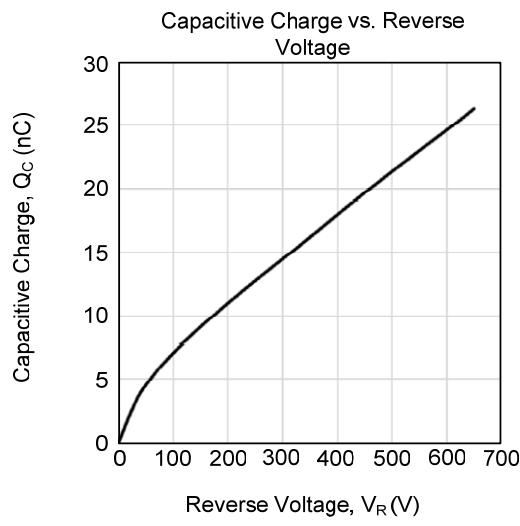
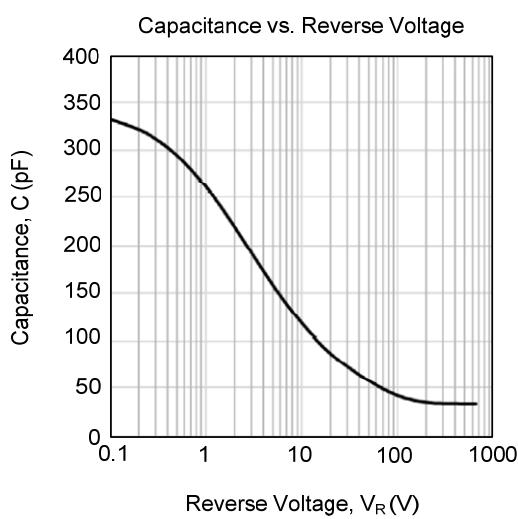
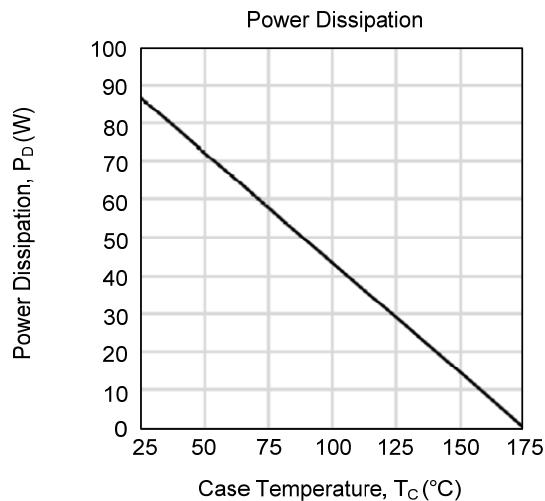
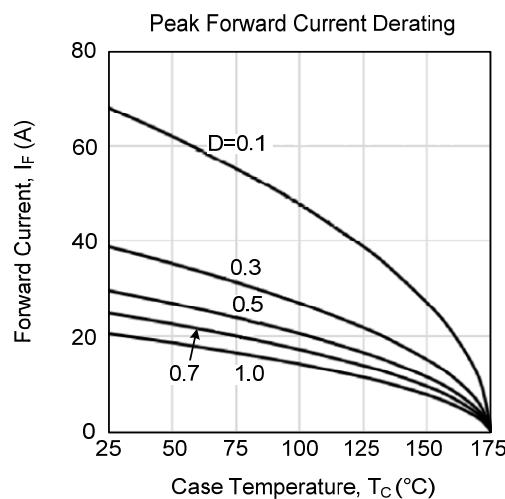
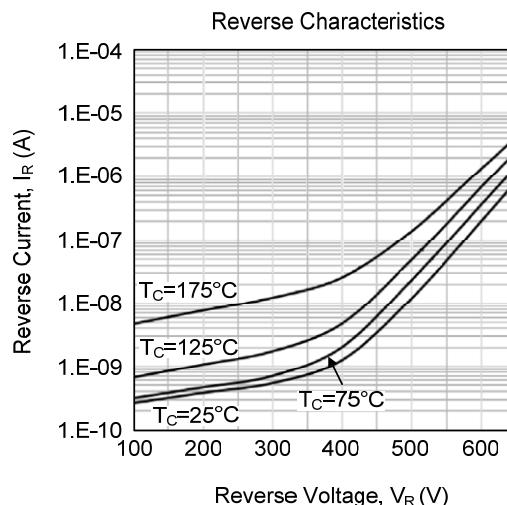
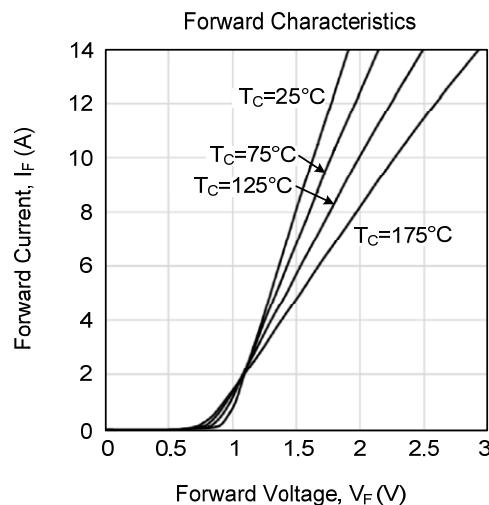
PARAMETER	SYMBOL	RATINGS		UNIT
Junction to Case	TO-220-2	θ_{JC}	1.7	$^\circ\text{C}/\text{W}$
	TO-220F-2		3.125	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS

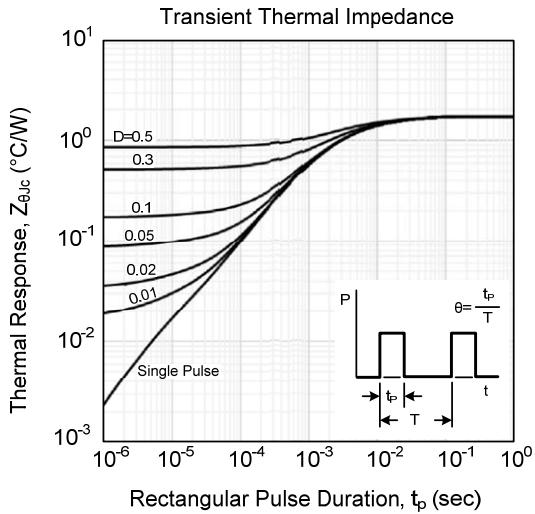
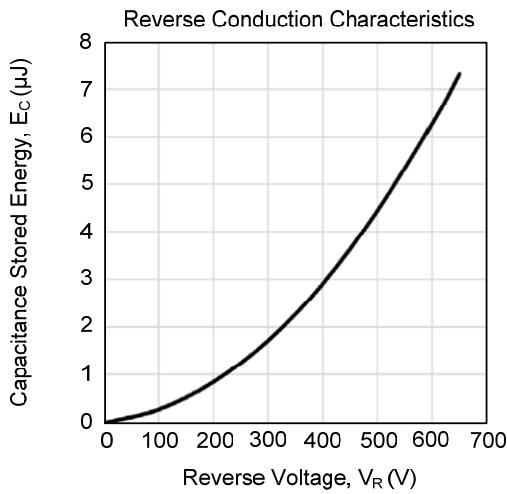
(Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC Blocking Voltage	V_{DC}	$T_c=25^\circ\text{C}$	650			V
Forward Voltage	V_F	$I_F=3.0\text{A}, T_c=25^\circ\text{C}$		1.16		V
		$I_F=6.0\text{A}, T_c=25^\circ\text{C}$		1.34	1.5	V
		$I_F=6.0\text{A}, T_c=175^\circ\text{C}$		1.66		V
Reverse Current	I_R	$V_R=650\text{V}, T_c=25^\circ\text{C}$		1.2	50	μA
		$V_R=650\text{V}, T_c=175^\circ\text{C}$		4.5		μA
Total Capacitive Charge	Q_C	$V_R=400\text{V}$		18		nC
Total Capacitance	C	$V_R=1.0\text{V}, T_c=25^\circ\text{C}, f=1\text{MHz}$		261		pF
		$V_R=200\text{V}, T_c=25^\circ\text{C}, f=1\text{MHz}$		35		pF
		$V_R=400\text{V}, T_c=25^\circ\text{C}, f=1\text{MHz}$		33		pF
Capacitance Stored Energy	E_C	$V_R=400\text{V}$		2.9		μJ

■ TYPICAL CHARACTERISTICS



- TYPICAL CHARACTERISTICS (Cont.)



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